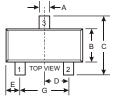


### **DUAL SURFACE MOUNT SWITCHING DIODE**

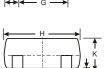
### **Features**

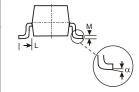
- Low Forward Voltage
- Small package
- Fast reverse recovery time
- Marking Code:A4



# Maximum Ratings @ T<sub>A</sub> = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	V <sub>R</sub>	75	V
Average Forward Current	Io	200	mA
Maximum Peak Forward Current	I <sub>FM</sub>	300	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s at t = 1 µs	I <sub>FSM</sub>	1 2	А
Power Dissipation	Pd	350	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 150	۰C





SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
C	2.30	2.50			
D	0.89	1.03			
E	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

## **Equivalent Circuit**



# Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 1$ mA at $I_F = 10$ mA at $I_F = 50$ mA at $I_F = 150$ mA	V <sub>F</sub> V <sub>F</sub> V <sub>F</sub>	- - -	715 855 1 1.25	mV mV V
Reverse Current at $V_R$ = 20 V at $V_R$ = 75 V at $V_R$ = 25 V, $T_J$ = 150 °C at $V_R$ = 75 V, $T_J$ = 150 °C	lr Ir Ir Ir	- - -	25 2.5 30 50	nA µA µA µA
Reverse Breakdown Voltage at $I_R$ = 100 $\mu$ A	V <sub>(BR)R</sub>	75	-	V
Total Capacitance at $V_R = 0$ , $f = 1$ MHz	Ст	-	2	pF
Reverse Recovery Time at $I_F$ = 10 mA, $V_R$ = 6 V, $I_{RR}$ = 1 mA, $R_L$ = 100 $\Omega$	t <sub>rr</sub>	-	4	ns



# **DUAL SURFACE MOUNT SWITCHING DIODE**

### **TYPICAL TRANSIENT CHARACTERISTICS**

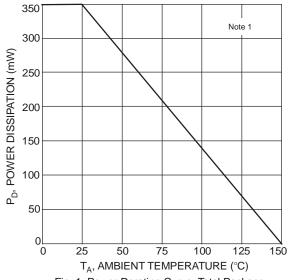
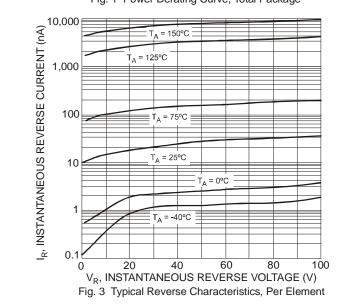
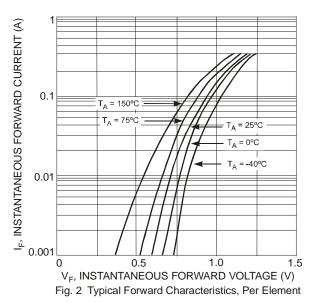


Fig. 1 Power Derating Curve, Total Package





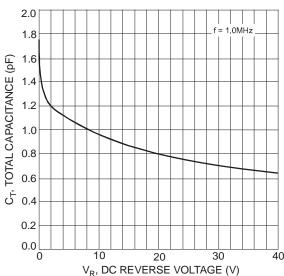


Fig. 4 Total Capacitance vs. Reverse Voltage, Per Element

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#### **DUAL SURFACE MOUNT SWITCHING DIODE**

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